Notice of Allowability	Application No.	Applicant(s)	Applicant(s)	
	10/605,607	HO ET AL.		
	Examiner	Art Unit		
	Eric B. Chen	1765		
The MAILING DATE of this communication appeall claims being allowable, PROSECUTION ON THE MERITS IS herewith (or previously mailed), a Notice of Allowance (PTOL-85) NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RI of the Office or upon petition by the applicant. See 37 CFR 1.313	(OR REMAINS) CLOSED in or other appropriate commember GHTS. This application is	in this application. If not inclu unication will be mailed in du	ided e course. THIS	
1. This communication is responsive to <u>8/19/05</u> .				
2. The allowed claim(s) is/are 2-9 and 11-18.				
 Acknowledgment is made of a claim for foreign priority unally all b) Some* c) None of the: Certified copies of the priority documents have Certified copies of the priority documents have Copies of the certified copies of the priority documents have International Bureau (PCT Rule 17.2(a)). 	been received. been received in Applicati	on No	cation from the	
Applicant has THREE MONTHS FROM THE "MAILING DATE" noted below. Failure to timely comply will result in ABANDONM THIS THREE-MONTH PERIOD IS NOT EXTENDABLE.		e a reply complying with the r	requirements	
4. A SUBSTITUTE OATH OR DECLARATION must be subminFORMAL PATENT APPLICATION (PTO-152) which give			NOTICE OF	
 5. CORRECTED DRAWINGS (as "replacement sheets") must (a) including changes required by the Notice of Draftspers 1) hereto or 2) to Paper No./Mail Date (b) including changes required by the attached Examiner's Paper No./Mail Date Identifying indicia such as the application number (see 37 CFR 1 each sheet. Replacement sheet(s) should be labeled as such in the state of the property of of the property	son's Patent Drawing Revie s Amendment / Comment of .84(c)) should be written on	or in the Office action of the drawings in the front (not t	he back) of	
6. DEPOSIT OF and/or INFORMATION about the depo attached Examiner's comment regarding REQUIREMENT			. Note the	
Attachment(s) 1. Notice of References Cited (PTO-892) 2. Notice of Draftperson's Patent Drawing Review (PTO-948) 3. Information Disclosure Statements (PTO-1449 or PTO/SB/0 Paper No./Mail Date	6. Interview S Paper No	nformal Patent Application (P Summary (PTO-413), ./Mail Date s Amendment/Comment	TO-152) .	
4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	8. ⊠ Examiner's 9. □ Other	s Statement of Reasons for A	llowance	
	su	NADINE G. NORTON PERVISORY PATENT EXA Padin Monton	WINED	

DETAILED ACTION

Allowable Subject Matter

- 1. Claims 2-9 and 11-18 are allowed.
- 2. The following is an examiner's statement of reasons for allowance: the prior art fails to teach or suggest etching through said SOI layer, a buried insulator layer underneath said SOI layer, and a bulk silicon layer beneath said buried insulator layer using a single etch step, wherein said single step is sufficient to etch through said bulk silicon layer to a depth corresponding to a deep trench opening, wherein said etching is implemented with an HBr, NF₃ and O₂ etch chemistry. The closest prior art, Sell, discloses multiple etching steps by first etching through said SOI layer (47), and a bulk silicon layer (41) beneath said BOX layer (paragraph 0076; Figure 9) using an HBr, NF₃ and O₂ etch chemistry. Sell further discloses etching through a buried oxide (BOX) layer (46) underneath said SOI layer with an CHF₃/O₂ etch chemistry (paragraph 0076). In addition, Kleinhenz discloses a etching through said SOI layer (120), a buried insulator layer (110) underneath said SOI layer, and a bulk silicon layer (100) beneath said insulator layer a single etch step to a shallow depth (column 4, lines 12-23; Figure 4) with a CF₄, CHF₄, and O₂ etch chemistry (column 4, lines 23-26). However, there is no motivation of suggestion of etching through said SOI layer, a buried insulator layer underneath said SOI layer, and a bulk silicon layer beneath said buried insulator layer using a single etch step, wherein said single step is sufficient to etch through said bulk

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silicon layer to a depth corresponding to a deep trench opening, wherein said etching is implemented with an HBr, NF₃ and O₂ etch chemistry.

3. Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

Response to Arguments

- 4. In view of Applicants' amendments (Amendments to the Claims, page 2), filed Aug. 19, 2005, the rejection of claims 2-9 and 11-18 under 35 U.S.C. 112, second paragraph, have been withdrawn.
- 5. In view of Applicants' amendments (Amendments to the Claims, pages 2-3), filed Aug. 19, 2005, the rejection of claims 4 and 13 under 35 U.S.C. 103(a), as being unpatentable over Kleinhenz, in view of Rossnagel, have been withdrawn.
- 6. In view of Applicants' amendments (Amendments to the Claims, pages 2-3), filed Aug. 19, 2005, the rejection of claims 5 and 14 under 35 U.S.C. 103(a), as being unpatentable over Kleinhenz, in view of Wolf, have been withdrawn.
- 7. In view of Applicants' amendments (Amendments to the Claims, pages 2-3), filed Aug. 19, 2005, the rejection of claims 6-9 and 15-18 under 35 U.S.C. 103(a), as being unpatentable over Kleinhenz, in view of Wolf, in further view of Sell, have been withdrawn.

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Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Eric B. Chen whose telephone number is (571) 272-2947. The examiner can normally be reached on Monday through Friday, 8AM to 4:30PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nadine G. Norton can be reached on (571) 272-1465. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

EBC ~

Sept. 12, 2005

RIPERVISORY P.

Madine Morlon

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